

either one of said first charged particle beam or said second charged particle beam is a primary sample to be inspected, and the other is a secondary charged particle beam generated from said sample by the irradiation of said primary charged particle beam.

A3 30. (Amended) A method for manufacturing a device using an inspection apparatus defined by any one of claims 26 or 27, in which a pattern inspection is performed in the device manufacturing processes.

A4 44. (Amended) A charged particle beam apparatus in accordance with either of claim 41 or 42, in which said dividers are arranged in two locations in the proximity of the charged particle beam irradiating location and the proximity of the hydrostatic bearing.

45. (Amended) A charged particle beam apparatus in accordance with either of claim 41 or 42, in which the gas supplied to the hydrostatic bearing of said stage is nitrogen or an inert gas.

46. (Amended) A charged particle beam apparatus in accordance with either of claim 41 or 42, in which a surface treatment is applied to at least the surface of a part facing the hydrostatic bearing in said XY stage so as to reduce the amount of gas to be desorbed.

47. (Amended) A wafer defect inspection apparatus for inspecting the surface of a wafer for defects by using the apparatus disclosed in either of claim 41 or 42.

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48. (Amended) An exposing apparatus for delineating the circuit pattern of a semiconductor device on the surface of a semiconductor wafer or a reticle by using the apparatus disclosed in either of claim 41 or 42.

49. (Amended) A semiconductor manufacturing method for manufacturing a semiconductor by using the apparatus disclosed in either of claim 41 or 42.

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54. (Amended) A semiconductor manufacturing method including a process for inspecting a finished wafer or a wafer under processing for defects by using an inspection apparatus in accordance with any of claims 50 to 52.

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59. (Amended) A semiconductor manufacturing method for manufacturing a semiconductor by using the apparatus in accordance with either of claims 55 or 56.